

PATENT ABSTRACTS OF JAPAN

(11)Publication number : **2000-228527**
(43)Date of publication of application : **15.08.2000**

(51)Int.CI. H01L 29/786
H01L 21/336

(21)Application number : 11-345498
(22)Date of filing : 03.12.1999

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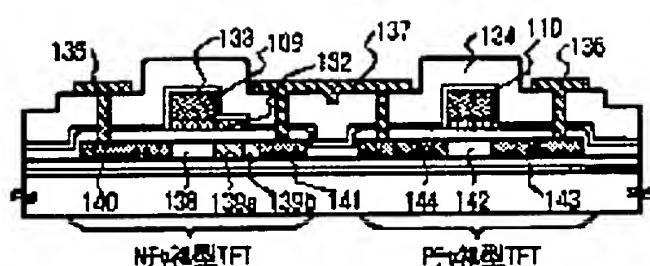
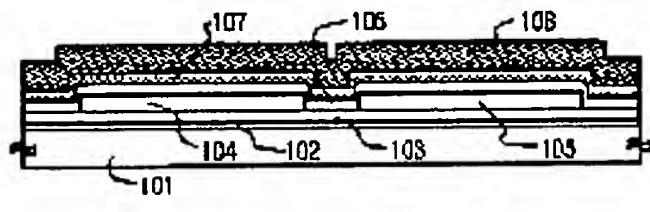
(30)Priority
Priority number : 10344746 Priority date : 03.12.1998 Priority country : JP

(54) SEMICONDUCTOR DEVICE AND MANUFACTURE THEREOF

(57) Abstract:

PROBLEM TO BE SOLVED: To obtain good characteristics in both states of ON and OFF, by allowing a gate electrode to have the first and second layers, a semiconductor layer to have a channel forming region, a first and second impurity regions, and a part 1 of the second impurity region to be overlaid with the first layer of the gate electrode.

SOLUTION: A first conductive film 107 to be the first layer of a gate electrode and a second conductive layer 108 to be the second layer of the gate electrode are formed on the surface of a gate insulating film 106. The first conductive film 107 is a semiconductor film containing Si or Ge as a main component. The second conductive film 108 contains Ti, Ta, W and Mo as main components. A channel forming region 138, first impurity regions 140, 141 and a second impurity region are formed in an n-channel TFT (a thin film transistor) of a CMOS circuit. Here, in the second impurity region, a region 139a (GOLD region) which superimposes with the gate electrode and a region 139b (LDD region) which does not overlap the gate electrode are respectively formed.



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[Date of request for examination]
[Date of sending the examiner's decision of rejection]
[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]
[Date of final disposal for application]
[Patent number]
[Date of registration]
[Number of appeal against examiner's decision of rejection]
[Date of requesting appeal against examiner's decision of rejection]
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